

V.H.F. POWER TRANSISTOR

N-P-N silicon planar epitaxial transistor intended for use in class-A, B and C operated h.f. and v.h.f. transmitters with a nominal supply voltage of 28 V. The transistor is resistance stabilized and is guaranteed to withstand severe load mismatch conditions.

It has a 3/8" capstan envelope with a ceramic cap. All leads are isolated from the stud.

QUICK REFERENCE DATA

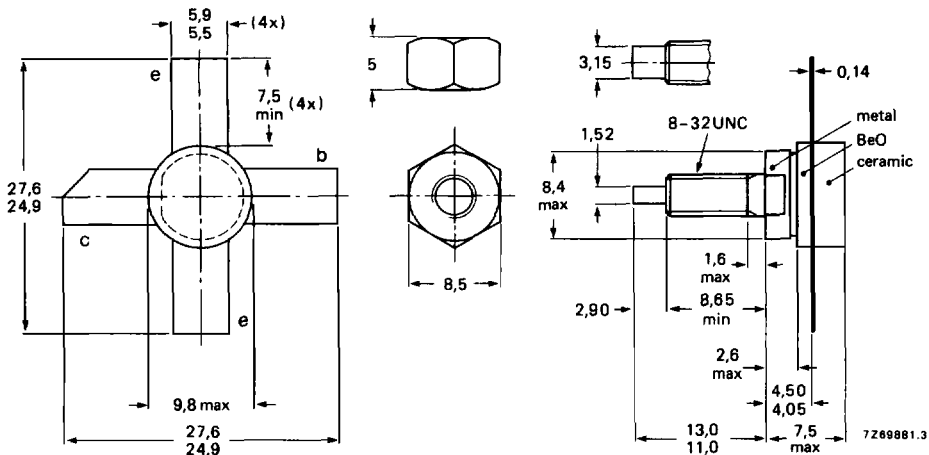
R.F. performance up to $T_h = 25^\circ\text{C}$ in an unneutralized common-emitter class-B circuit

mode of operation	V_{CE} V	f MHz	P_L W	G_p dB	η %	\bar{z}_i Ω	\bar{Y}_L mS
c.w.	28	175	15	> 10	> 65	$1,4 + j1,85$	$33 - j27,5$

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-120.



Torque on nut: min. 0,75 Nm
(7,5 kg cm)
max. 0,85 Nm
(8,5 kg cm)

Diameter of clearance hole in heatsink: max. 4,2 mm.
Mounting hole to have no burrs at either end.
De-burring must leave surface flat; do not chamfer or
countersink either end of hole.

When locking is required an adhesive is preferred instead of a lock washer.

PRODUCT SAFETY This device incorporates beryllium oxide, the dust of which is toxic. The device is entirely safe provided that the BeO disc is not damaged.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage ($V_{BE} = 0$)
peak value

V_{CESM} max. 65 V

Collector-emitter voltage (open base)

V_{CEO} max. 36 V

Emitter-base voltage (open collector)

V_{EBO} max. 4 V

Collector current (average)

$I_C(AV)$ max. 1,75 A

Collector current (peak value); $f > 1$ MHz

I_{CM} max. 5,0 A

R.F. power dissipation ($f > 1$ MHz); $T_{mb} = 25$ °C

P_{rf} max. 36 W

Storage temperature

T_{stg} -65 to + 150 °C

Operating junction temperature

T_j max. 200 °C

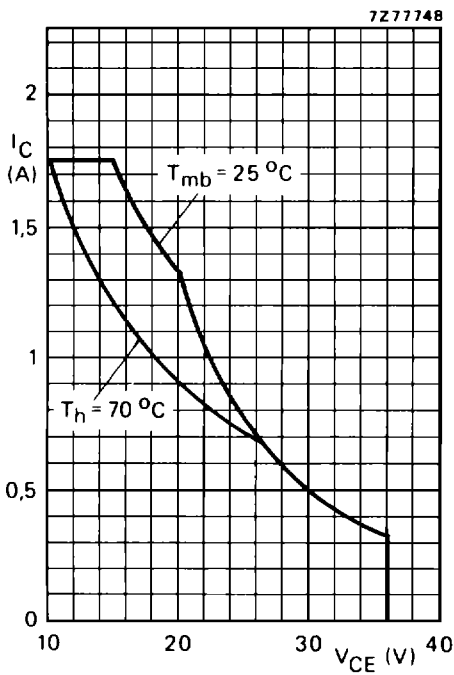


Fig. 2 D.C. SOAR.

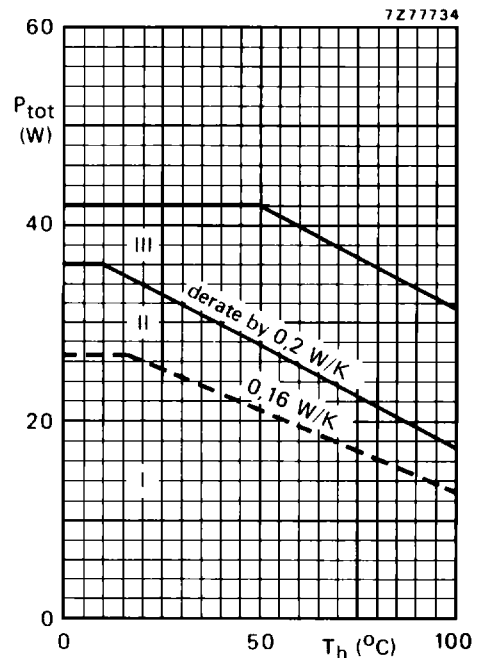


Fig. 3 R.F. power dissipation; $V_{CE} \leq 28$ V; $f > 1$ MHz.

- I Continuous d.c. operation
- II Continuous r.f. operation
- III Short-time operation during mismatch

THERMAL RESISTANCE (dissipation = 15 W; $T_{mb} = 77$ °C, i.e. $T_h = 70$ °C)

From junction to mounting base (d.c. dissipation)

$R_{th j-mb(dc)}$ = 6,55 K/W

From junction to mounting base (r.f. dissipation)

$R_{th j-mb(rf)}$ = 4,95 K/W

From mounting base to heatsink

$R_{th mb-h}$ = 0,45 K/W

CHARACTERISTICS $T_j = 25\text{ }^\circ\text{C}$

Collector-emitter breakdown voltage

 $V_{BE} = 0; I_C = 5\text{ mA}$ $V_{(BR)CES} > 65\text{ V}$

Collector-emitter breakdown voltage

open base; $I_C = 25\text{ mA}$ $V_{(BR)CEO} > 36\text{ V}$

Emitter-base breakdown voltage

open collector; $I_E = 2\text{ mA}$ $V_{(BR)EBO} > 4\text{ V}$

Collector cut-off current

 $V_{BE} = 0; V_{CE} = 36\text{ V}$ $I_{CES} < 2\text{ mA}$ Second breakdown energy; $L = 25\text{ mH}; f = 50\text{ Hz}$

open base

 $R_{BE} = 10\text{ }\Omega$ $ES_{BO} > 2,5\text{ mJ}$ $ES_{BR} > 2,5\text{ mJ}$

D.C. current gain*

 $I_C = 0,7\text{ A}; V_{CE} = 5\text{ V}$ h_{FE} typ. 50
10 to 100

Collector-emitter saturation voltage*

 $I_C = 2\text{ A}; I_B = 0,4\text{ A}$ V_{CEsat} typ. 0,65 VTransition frequency at $f = 100\text{ MHz}$ * $-I_E = 0,7\text{ A}; V_{CB} = 28\text{ V}$ $-I_E = 2\text{ A}; V_{CB} = 28\text{ V}$ f_T typ. 650 MHz f_T typ. 625 MHzCollector capacitance at $f = 1\text{ MHz}$ $I_E = I_e = 0; V_{CB} = 28\text{ V}$ C_c typ. 18 pFFeedback capacitance at $f = 1\text{ MHz}$ $I_C = 100\text{ mA}; V_{CE} = 28\text{ V}$ C_{re} typ. 12,8 pF

Collector-stud capacitance

 C_{cs} typ. 2 pF* Measured under pulse conditions: $t_p \leq 200\text{ }\mu\text{s}; \delta \leq 0,02$.

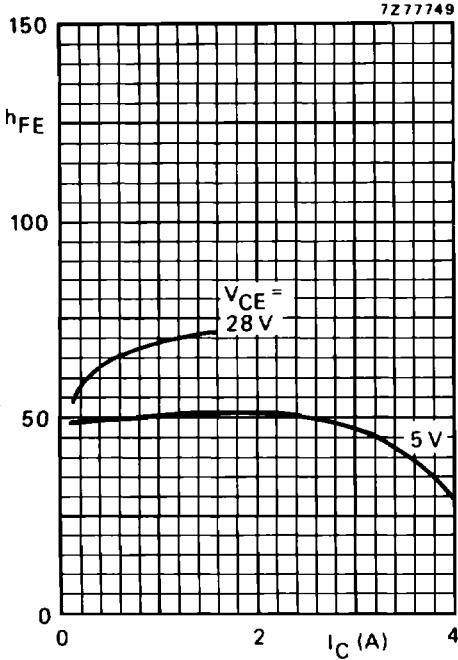


Fig. 4 Typical values; $T_j = 25^\circ\text{C}$.

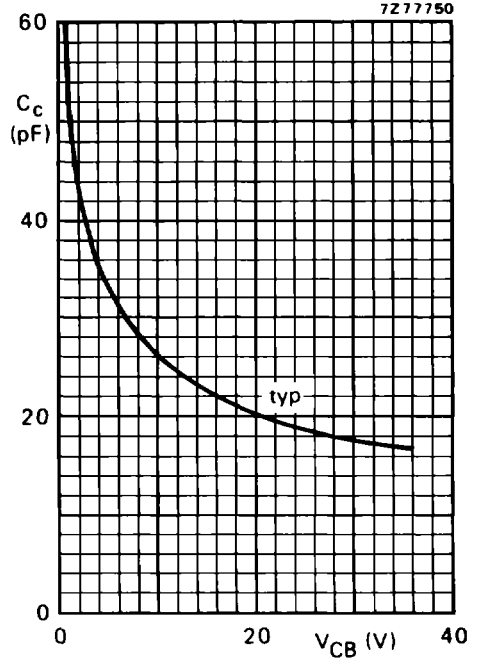


Fig. 5 $I_E = I_e = 0$; $f = 1\text{ MHz}$; $T_j = 25^\circ\text{C}$.

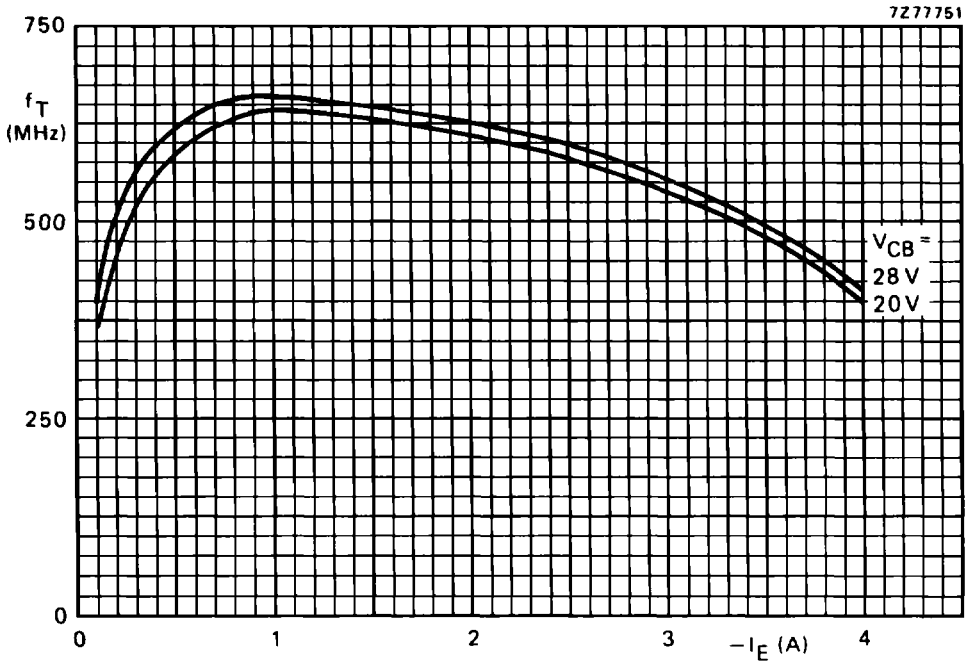


Fig. 6 Typical values; $f = 100\text{ MHz}$; $T_j = 25^\circ\text{C}$.

APPLICATION INFORMATION

R.F. performance in c.w. operation (unneutralized common-emitter class-B circuit)

 $T_h = 25\text{ }^\circ\text{C}$

f (MHz)	V_{CE} (V)	P_L (W)	P_S (W)	G_p (dB)	I_C (A)	η (%)	\bar{z}_i (Ω)	\bar{Y}_L (mS)
175	28	15	< 1,5	> 10	< 0,83	> 65	$1,4 + j1,85$	$33 - j27,5$

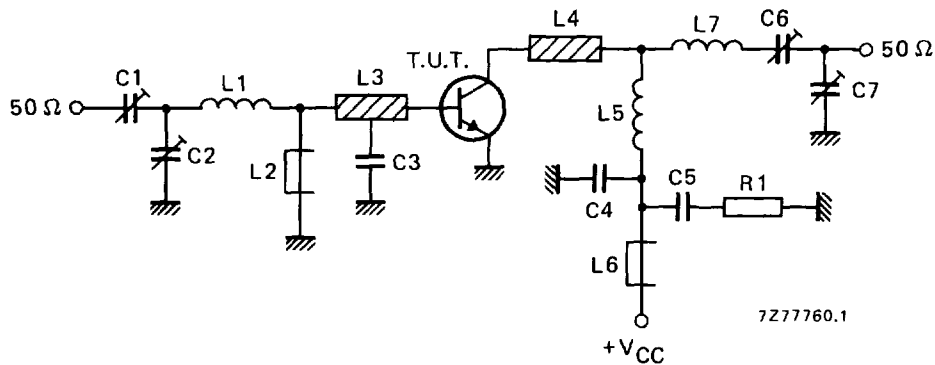


Fig. 7 Test circuit; c.w. class-B.

List of components:

C1 = C7 = 2,5 to 20 pF film dielectric trimmer (cat. no. 2222 809 07004)

C2 = C6 = 5 to 60 pF film dielectric trimmer (cat. no. 2222 809 07011)

C3 = 27 pF ceramic capacitor (500 V)

C4 = 120 pF ceramic capacitor (500 V)

C5 = 100 nF polyester capacitor

L1 = 1 turn Cu wire (1,6 mm); int. dia. 8,4 mm; leads 2 x 5 mm

L2 = 7 turns closely wound enamelled Cu wire (0,5 mm); int. dia. 3 mm; leads 2 x 5 mm

L3 = L8 = Ferroxcube wide band h.f. choke, grade 3B (cat. no. 4312 020 36640)

L4 = L5 = strip (12 mm x 6 mm); tap for C3 at 5 mm from transistor

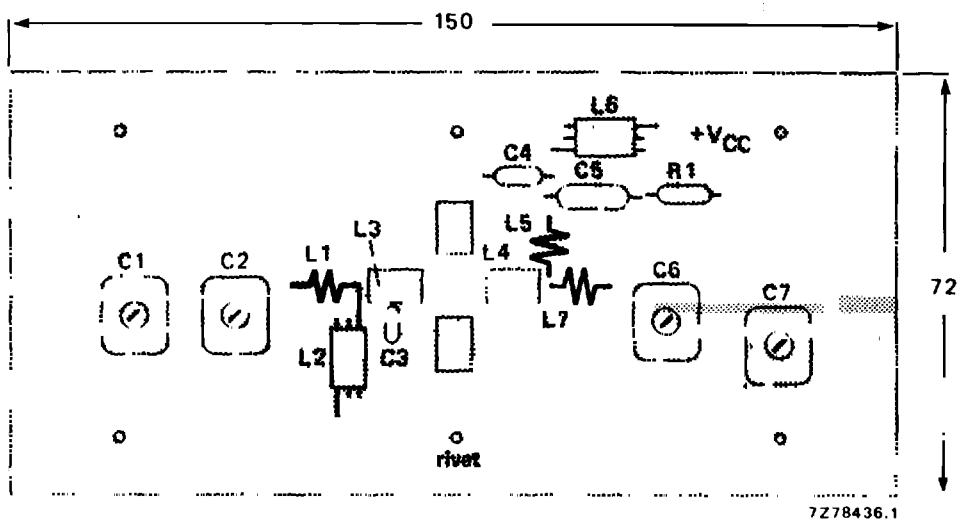
L6 = 3 turns closely wound enamelled Cu wire (1,0 mm); int. dia. 9,0 mm; leads 2 x 5 mm

L7 = 3 turns closely wound enamelled Cu wire (1,0 mm); int. dia. 8,2 mm; leads 2 x 5 mm

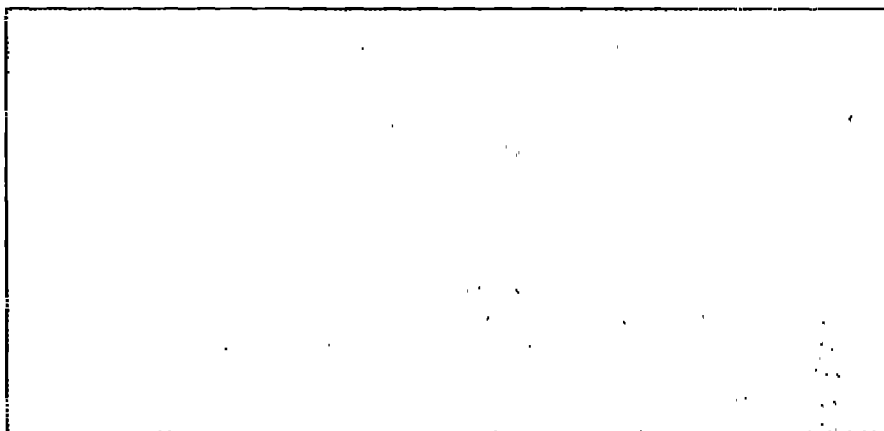
L4 and L5 are strips on a double Cu-clad printed-circuit board with epoxy fibre-glass dielectric, thickness 1/16".

R1 = R2 = 10 Ω carbon resistor

Component layout and printed-circuit board for 175 MHz test circuit see Fig. 8.



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Fig. 8 Component layout and printed-circuit board for 175 MHz test circuit.

The circuit and the components are situated on one side of the epoxy fibre-glass board, the other side being fully metallized to serve as earth. Earth connections are made by means of hollow rivets, whilst under the emitter leads Cu straps are used for a direct contact between upper and lower sheets.

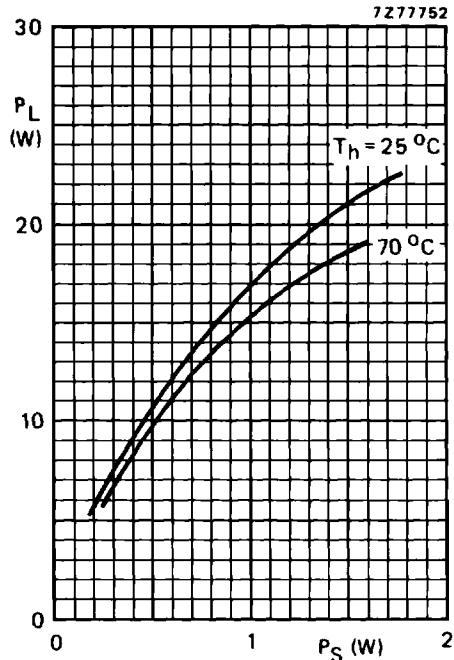


Fig. 9 Typical values; $V_{CE} = 28\text{ V}$; $f = 175\text{ MHz}$.

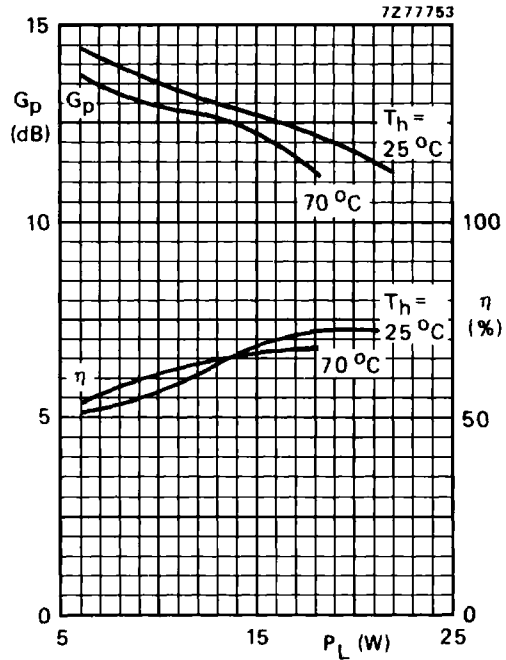


Fig. 10 Typical values; $V_{CE} = 28\text{ V}$; $f = 175\text{ MHz}$.

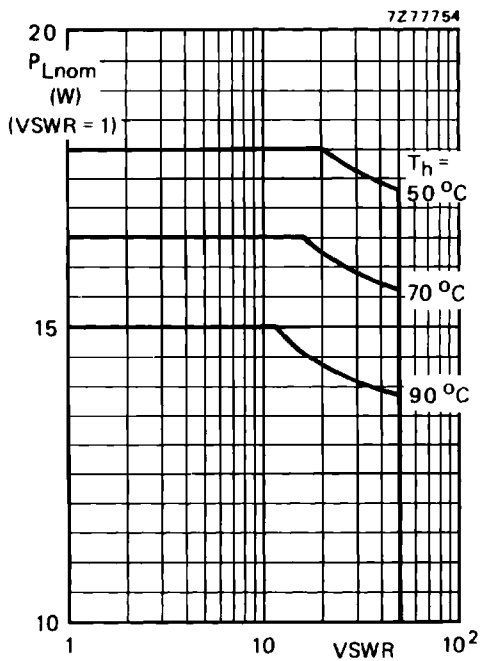


Fig. 11 R.F. SOAR; c.w. class-B operation; $f = 175\text{ MHz}$; $V_{CE} = 28\text{ V}$; $R_{th\text{ mb-h}} = 0,45\text{ K/W}$. The graph shows the permissible output power under nominal conditions (VSWR = 1) as a function of the expected VSWR during short-time mismatch conditions with heatsink temperatures as parameter.

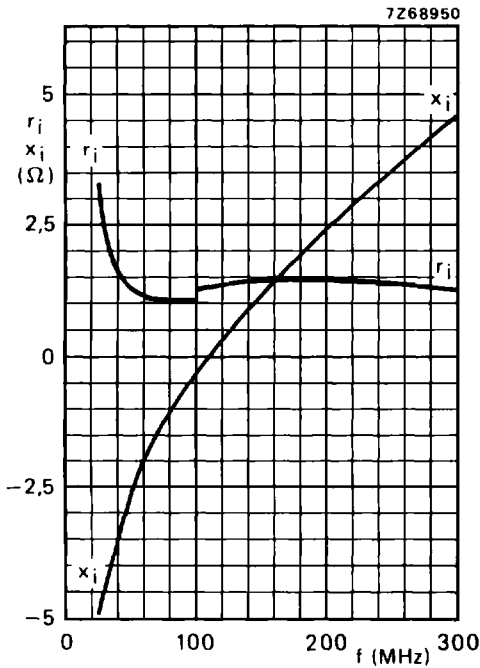


Fig. 12 Input impedance (series components).

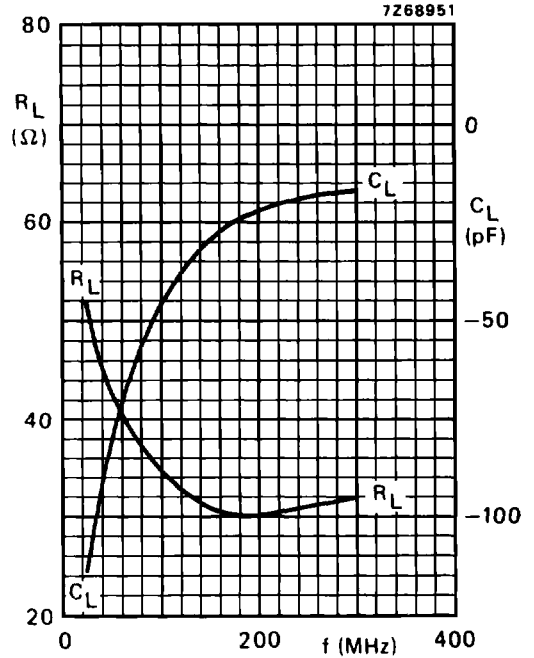


Fig. 13 Load impedance (parallel components).

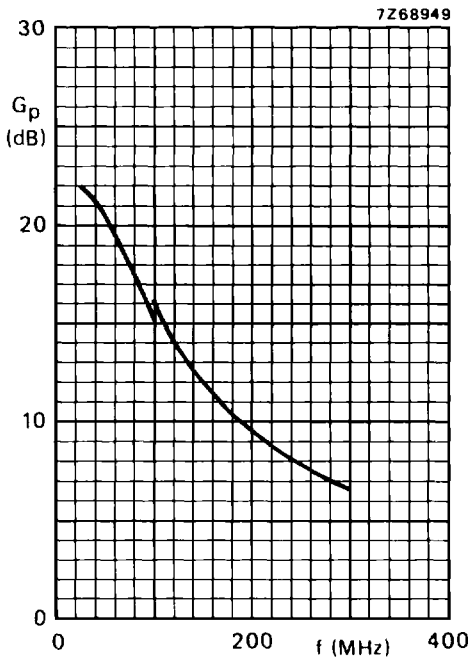


Fig. 14.

Conditions for Figs 12, 13 and 14.

Typical values; $V_{CE} = 28$ V; $P_L = 15$ W;

$T_h = 25$ °C.

OPERATING NOTE

Below 100 MHz a base-emitter resistor of 10 Ω is recommended to avoid oscillation.

This resistor must be effective for r.f. only.